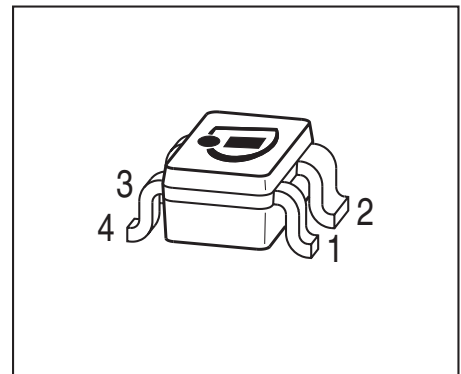


Low Noise Silicon Bipolar RF Transistor

- For low noise, high-gain amplifiers up to 2 GHz
- For linear broadband amplifiers
- $f_T = 8 \text{ GHz}$, $NF_{\min} = 1 \text{ dB}$ at 900 MHz
- Pb-free (RoHS compliant) package
- Qualification report according to AEC-Q101 available



ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Type	Marking	Pin Configuration						Package
BFP193W	RCs	1 = E	2 = C	3 = E	4 = B	-	-	SOT343

Maximum Ratings at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	12	V
Collector-emitter voltage	V_{CES}	20	
Collector-base voltage	V_{CBO}	20	
Emitter-base voltage	V_{EBO}	2	
Collector current	I_C	80	mA
Base current	I_B	10	
Total power dissipation ¹⁾ $T_S \leq 66^\circ\text{C}$	P_{tot}	580	mW
Junction temperature	T_J	150	$^\circ\text{C}$
Storage temperature	T_{Stg}	-55 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ²⁾	R_{thJS}	145	K/W

¹⁾ T_S is measured on the collector lead at the soldering point to the pcb

²⁾ For the definition of R_{thJS} please refer to Application Note AN077 (Thermal Resistance Calculation)

Electrical Characteristics at $T_A = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 1\text{ mA}$, $I_B = 0$	$V_{(BR)CEO}$	12	-	-	V
Collector-emitter cutoff current $V_{CE} = 20\text{ V}$, $V_{BE} = 0$	I_{CES}	-	-	100	μA
Collector-base cutoff current $V_{CB} = 10\text{ V}$, $I_E = 0$	I_{CBO}	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 1\text{ V}$, $I_C = 0$	I_{EBO}	-	-	1	μA
DC current gain $I_C = 30\text{ mA}$, $V_{CE} = 8\text{ V}$, pulse measured	h_{FE}	70	100	140	-

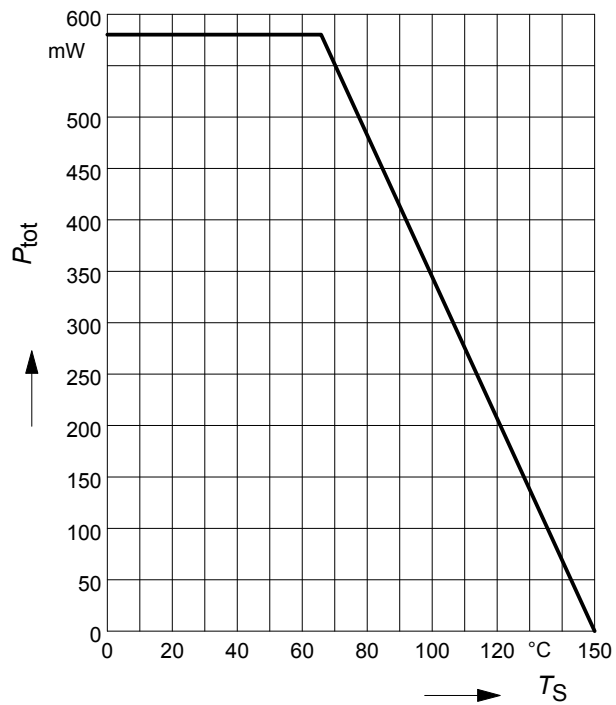
Electrical Characteristics at $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling)					
Transition frequency $I_C = 50\text{ mA}$, $V_{CE} = 8\text{ V}$, $f = 500\text{ MHz}$	f_T	6	8	-	GHz
Collector-base capacitance $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$, $V_{BE} = 0$, emitter grounded	C_{cb}	-	0.63	0.9	pF
Collector emitter capacitance $V_{CE} = 10\text{ V}$, $f = 1\text{ MHz}$, $V_{BE} = 0$, base grounded	C_{ce}	-	0.36	-	
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$, $f = 1\text{ MHz}$, $V_{CB} = 0$, collector grounded	C_{eb}	-	2.25	-	
Minimum noise figure $I_C = 10\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_{Sopt}$, $f = 900\text{ MHz}$ $f = 1.8\text{ GHz}$	NF_{min}	- -	1 1.6	- -	dB
Power gain, maximum available ¹⁾ $I_C = 30\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_{Sopt}$, $Z_L = Z_{Lopt}$, $f = 900\text{ MHz}$ $f = 1.8\text{ GHz}$	G_{ma}	- -	20.5 13.5	- -	
Transducer gain $I_C = 30\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_L = 50\Omega$, $f = 900\text{ MHz}$ $f = 1.8\text{ GHz}$	$ S_{21e} ^2$	- -	15 9	- -	
Third order intercept point at output ²⁾ $I_C = 30\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_L = 50\text{ }\Omega$, $f = 0.9\text{ GHz}$	IP_3	-	29.5	-	dBm
1dB Compression point $I_C = 30\text{ mA}$, $V_{CE} = 8\text{ V}$, $Z_S = Z_L = 50\text{ }\Omega$, $f = 0.9\text{ GHz}$	P_{-1dB}	-	13	-	

¹⁾ $G_{ma} = |S_{21} / S_{12}| (k - (k^2 - 1)^{1/2})$
²⁾ IP_3 value depends on termination of all intermodulation frequency components.

Termination used for this measurement is 50Ω from 0.2 MHz to 12 GHz

Total power dissipation $P_{\text{tot}} = f(T_S)$



[illegible]

Diagram illustrating the marking on a 16-pin DIP package:

- Date code (YM):** 2005, June (indicated by '65')
- Type code:** XY
- Manufacturer:** s (Infineon logo is shown next to it)
- Pin 1:** Indicated by an arrow pointing to the bottom-left pin.

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